



[10191/1993]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Richard SPITZ et al.

Serial No. : 09/914,404

Filed : December 13, 2001

For : **METHOD FOR PRODUCING HEAVILY-DOPED SEMICONDUCTOR COMPONENTS**

Group Art Unit : 2823

Examiner : Michelle Estrada

Commissioner for Patents
Washington, D.C. 20231
BOX AF

I hereby certify that this correspondence is in compliance with the United States Postal Service as to its form and content and is acceptable for the Commissioner of Patents and Trademark Office.

Date 3/5/03

Atty's Signature R. L. Mayer

RICHARD L. MAYER
KENTON & KENTON

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AMENDMENT AFTER FINAL OFFICE ACTION

SIR:

In response to the Final Office Action mailed on November 20, 2002, please reconsider the above-identified application based on the following:

IN THE CLAIMS:

Please amend without prejudice the claims as follows:

13. (Twice Amended) A method for producing a semiconductor component in which at least one doped region is introduced into a semiconductor wafer, comprising the steps of:

applying a solid glass layer provided with a dopant on at least one of two sides of the semiconductor wafer;

heating the semiconductor wafer to a high temperature while the glass layer is applied so that the dopant from the solid glass layer penetrates into the semiconductor wafer to produce the at least one doped region;

removing the solid glass layer; and

providing the dopant at a dosage of at least $10^{17}/\text{cm}^2$ in the at least one doped region.